NSN 5961-01-625-9167

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-625-9167 **Inclosure Material:** Glass **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 repetitive peak reverse voltage **Product Name:** Glass passivated fast efficent rectifier **Special Features:** 3.0 amperes forward current; high temperature metallurgically bonded construction; glass passivated cavity-free junction; superfast recovery time for high efficiency; low forward forward voltage, high current capability; low leakage current; high surge current capability; high temperature soldering guaranteed; case-solid glass body; terminals-plated axial leads; polarity-color band denotes cathode end; mounting position-any; weight-0.037 ounce Shelf Life: N/a **Unit Of Measure: Demilitarization:** No